

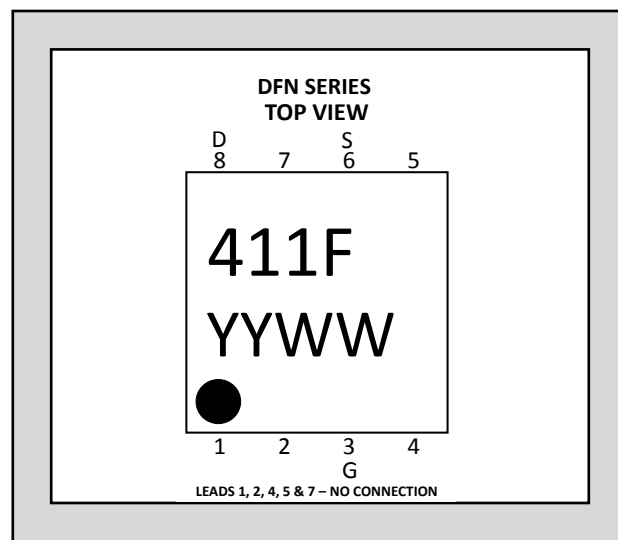


Improved Standard Products®

4117DFN SERIES

MINIATURE/NON MAGNETIC
8-PIN DFN PACKAGE
ULTRA-HIGH INPUT IMPEDANCE
N-CHANNEL JFET AMPLIFIER

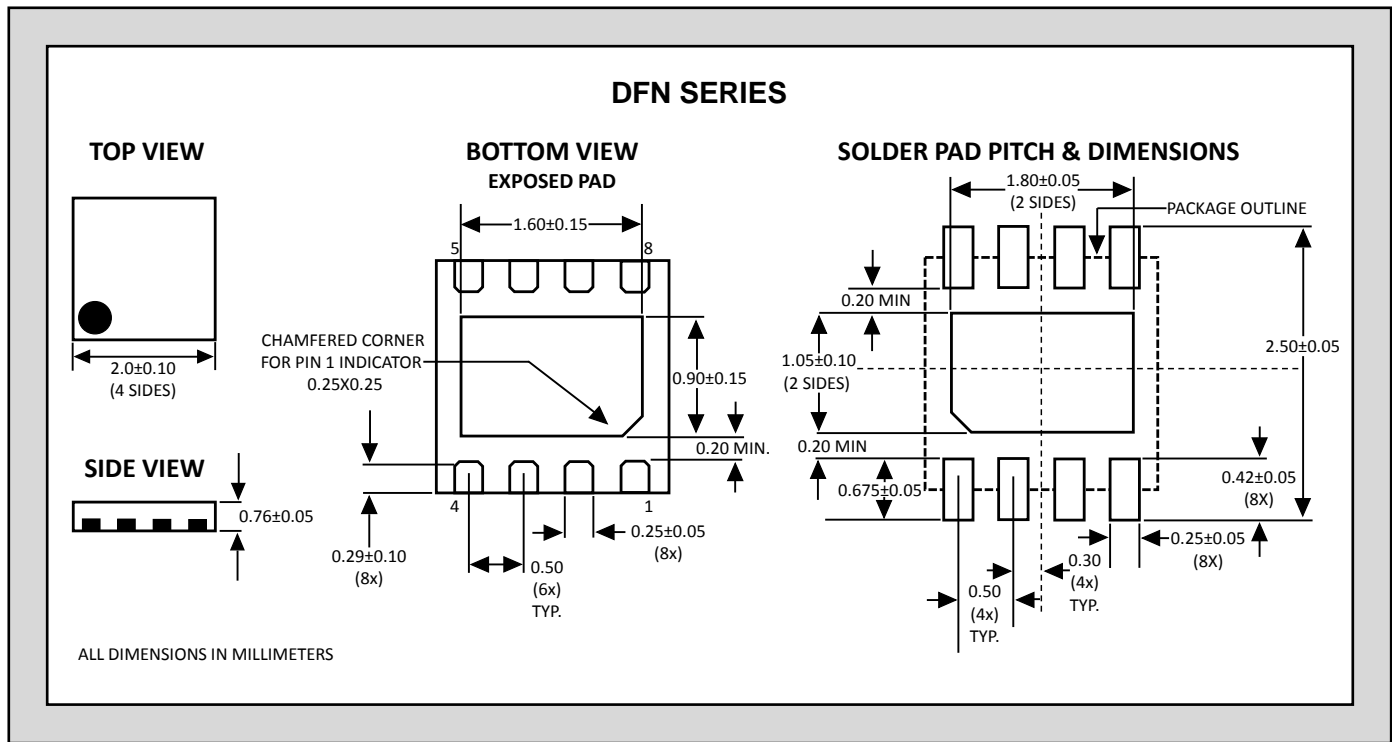
FEATURES	
LOW POWER	$I_{DSS} < 600 \mu A$ (4117DFN)
MINIMUM CIRCUIT LOADING	$I_{GSS} < 200 pA$ (4117DFN Series)
ABSOLUTE MAXIMUM RATINGS (NOTE 3)	
@ 25°C (unless otherwise noted)	
Gate-Source or Gate-Drain Voltage	-40V
Gate-Current	50mA
Total Device Dissipation (Derate 2.8mW/°C above 25°C)	300mW
Storage Temperature Range	-55°C to +150°C



ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

		4117DFN		4118DFN		4119DFN				
SYMBOL	CHARACTERISTIC	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	CONDITIONS	
BV _{GSS}	Gate-Source Breakdown Voltage	-40	--	-40	--	-40	--	V	I _G =-1μA, V _{DS} =0	
V _{GS(off)}	Gate-Source Cutoff Voltage	-0.6	-1.8	-1	-3	-2	-6		V _{DS} =10V, I _D =1nA	
I _{DSS}	Saturation Drain Current (NOTE 2)	0.03	0.60	0.08	0.60	0.20	0.80	mA	V _{DS} =10V, V _{GS} =0	
I _{GSS}	Gate Reverse Current	--	-200	--	-200	--	-200	pA	V _{GS} =-10V, V _{DS} =0V	
g _{fs}	Common-Source Forward Transconductance	70	450	80	650	100	700	μS	V _{DS} =10V, V _{GS} =0	f=1kHz
g _{os}	Common-Source Output Conductance (NOTE 4)	--	3	--	5	--	10			
C _{iss}	Common-Source Input Capacitance (NOTE 4)	--	3	--	3	--	3	pF		f=1MHz
C _{rss}	Common-Source Reverse Transfer Capacitance (NOTE 4)	--	1.5	--	1.5	--	1.5			

STANDARD PACKAGE DIMENSIONS:



NOTES:

1. Due to symmetrical geometry, these units may be operated with source and drain leads interchanged.
2. This parameter is measured during a 2 ms interval 100 ms after power is applied. (Not a JEDEC condition.)
3. Absolute maximum ratings are limiting values above which serviceability may be impaired.
4. Not production tested, guaranteed by design.

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